11.0   D.C. SPECIFICATIONS

11.1   Absolute Maximum Ratings

Storage Temperature .... −65°C to +150°C

Supply Voltage .... −0.5 to +8.0V

Voltage on Any Input .... GND − 2V to 6.5V

Voltage on Any Output.. GND − 0.5V to VCC + 0.5V

Power Dissipation .... 1 Watt

NOTICE: This is a production data sheet. The specifications are subject to change without notice.

WARNING: Stressing the device beyond the "Absolute Maximum Ratings" may cause permanent damage. These are stress ratings only. Operation beyond the "Operating Conditions" is not recommended and extended exposure beyond the "Operating Conditions" may affect device reliability.

11.2   D.C. Characteristics

$T_A = 0°C$ to $= 70°C$, $V_{CC} = +5V \pm 10\%$, $V_{SS} = AV_{SS} = 0V$

Symbol	Parameter	Min	Max	Unit	Test Conditions
V_{ILC}	Input Low Voltage, X1	−0.5	0.8	V	
V_{IHC}	Input High Voltage, X1	3.9	V_{CC} +0.5	V	
V_{IL}	Input Low Voltage (all pins except X1)	−0.5	0.8	V	
V_{IH}	Input High Voltage (all pins except X1)	2.0	V_{CC} +0.5	V	
V_{OL}	Output Low Voltage MFM		0.4	V	$I_{OL} = 2.5$ mA
	DRATE0−1		0.4	V	$I_{OL} = 6.0$ mA
	DB0−7, INT and DRQ		0.4	V	$I_{OL} = 12$ mA
	ME0~3, DS0−3, DIR, STP WRDATA, WE, HDSEL and DENSEL		0.4	V	$I_{OL} = 40$ mA
V_{OH}	Output High Voltage MFM	3.0		V	$I_{OH} = -2.5$ mA
	All Other Outputs	3.0		V	$I_{OH} = -4.0$ mA
	All Outputs	$V_{CC} - 0.4$		V	$I_{OH} = -100$ μA
I_{CC1} I_{CC2} I_{CC3} I_{CC4}	V_{CC} Supply Current (Total) 1 Mbps Data Rate, $V_{IL} = V_{SS}$, $V_{IH} = V_{CC}$ 1 Mbps Data Rate, $V_{IL} = 0.45$, $V_{IH} = 2.4$ 500 Kbps Data Rate, $V_{IL} = V_{SS}$, $V_{IH} = V_{CC}$ 500 Kbps Data Rate, $V_{IL} = 0.45$, $V_{IH} = 2.4$		45 50 35 40	mA mA mA mA	(Notes 1, 2) (Notes 1, 2) (Notes 1, 2) (Notes 1, 2)
I_{CCSB}	I_{CC} in Powerdown		60	μA	(Note 3)
I_{IL}	Input Load Current (all input pins)		10 −10	μA μA	$V_{IN} = V_{CC}$ $V_{IN} = 0V$
I_{OFL}	Data Bus Output Float Leakage		±10	μA	$0.45 < V_{OUT} < V_{CC}$

NOTES:
1. The data bus are the only inputs that may be floated.
2. Tested while reading a sync field of "00". Outputs not connected to D.C. Loads.
3. $V_{IL} = V_{SS}$, $V_{IH} = V_{CC}$; Outputs not connected to D.C. loads.

Capacitance

C_{IN}	Input Capacitance	10	pF	F = 1 MHz, T_A = 25°C
C_{IN1}	Clock Input Capacitance	20	pF	Sampled, not 100% Tested
$C_{I/O}$	Input/Output Capacitance	20	pF	

NOTE:
All pins except pins under test are tied to AC ground.

LOAD CIRCUIT

C_{load} = 50 pF for all logic outputs,
100 pF for the data bus.
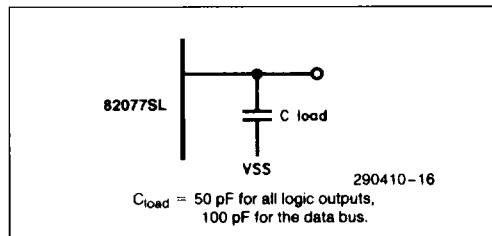
A. C. TESTING INPUT, OUTPUT WAVEFORM
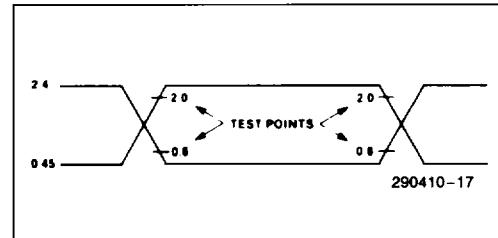

11.3 Oscillator
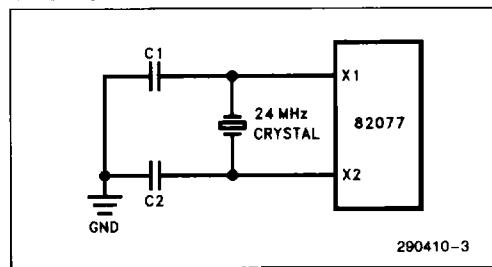
Figure 11-2. Crystal Oscillator Circuit

The 24 MHz clock can be supplied either by a crystal or a MOS level square wave. All internal timings are referenced to this clock or a scaled count which is data rate dependent.

The crystal oscillator must be allowed to run for 10 ms after VCC has reached 4.5V or exiting the POWERDOWN mode to guarantee that it is stable.

Crystal Specifications

Frequency:	24 MHz ±0.1%
Mode:	Parallel Resonant Fundamental Mode
Series Resistance:	Less than 40Ω
Shunt Capacitance:	Less than 5 pF